



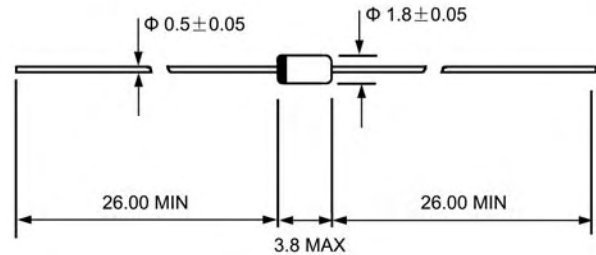
Reverse Voltage: 40Volts
Forward Current:0.35Amps



Features

For general purpose applications
 These diodes feature very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
 This diode is also available in the Mini-MELF

DO - 35



Dimensions in millimeters

Mechanical Data

Case: DO-35, glass case
 Polarity: Color band denotes cathode
 Weight: 0.005 ounces, 0.13 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

		BAT48	UNITS
Peak reverse voltage	V_R	40	V
Forward continuous current	I_F	350 ¹⁾	m A
Surge forward current at $t_p < 10$ ms	I_{FSM}	7.5 ¹⁾	A
Power dissipation	P_{tot}	330 ¹⁾	mW
Thermal resistance junction to ambient air	$R_{\theta JA}$	300 ¹⁾	/W
Junction temperature	T_j	-55 --- + 125	
Storage temperature range	T_{STG}	-55 --- + 150	

¹⁾Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature.



ELECTRICAL CHARACTERISTICS

		MIN	TYP	MAX	UNITS
Reverse breakover voltage at $I_R=100\mu A$	$V_{(BR)R}$	40	-	-	V
Forward voltage pulse test $t_p < 300\mu s, \delta < 2\%$ @ $I_F=0.1mA$ @ $I_F=1.0mA$ @ $I_F=10mA$ @ $I_F=50mA$ @ $I_F=200mA$ @ $I_F=500mA$	V_F	- - - - - -	- - - - - -	0.25 0.30 0.40 0.50 0.75 0.90	V
Leakage current pulse test $t_p < 300\mu s, \delta < 2\%$ @ $V_R=10V$ @ $V_R=10V, T_J=60$ @ $V_R=20V$ @ $V_R=20V, T_J=60$ @ $V_R=40V$ @ $V_R=40V, T_J=60$	I_R	- - - - - -	- - - - - -	2.0 15 5.0 25 25 50	μA
Junction capacitance at $V_R=1V$ $f=1MHz$	C_J	-	12	-	pF

¹⁾Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature(DO-35).

PACKAGE	SPQ/PCS	CARTON SPQ/PCS	CARTON SIZE/CM	CARTON GW/KG	CARTON NW/KG
DO-35	5000/AMMO	100000	41X28.5X38	14.57	13.07